1. General description

The 74LVC1G10 provides a low-power, low-voltage single 3-input NAND gate.

The inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V).
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information					
Type number	Package				
	Temperature range	Name	Description	Version	
74LVC1G10GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363	
74LVC1G10GV	–40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457	
74LVC1G10GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5$ mm	SOT886	
74LVC1G10GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891	
74LVC1G10GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115	
74LVC1G10GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202	

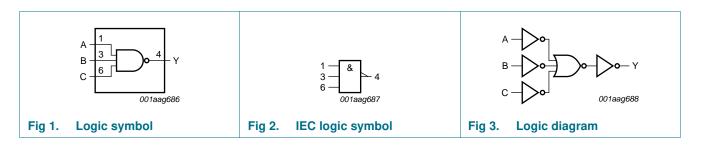
4. Marking

Table 2.	Marking
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Type number	Marking code ^[1]
74LVC1G10GW	YM
74LVC1G10GV	YM
74LVC1G10GM	YM
74LVC1G10GF	YM
74LVC1G10GN	YM
74LVC1G10GS	YM

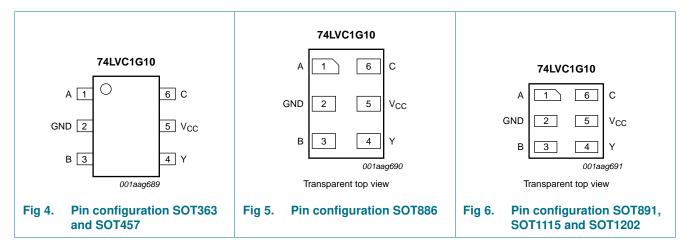
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
А	1	data input
GND	2	ground (0 V)
В	3	data input
Y	4	data output
V _{CC}	5	supply voltage
С	6	data input

7. Functional description

Table 4.Function table^[1]

Input			Output
Α	В	C	Y
Н	Н	Н	L
L	Х	Х	Н
Х	L	Х	Н
Х	Х	L	Н

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			•	10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V	-	±50	mA
Vo	output voltage	Active mode	[1][2] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	<u>[3]</u>	250	mW
T _{stg}	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 1.65 \text{ V}$ to 2.7 V	-	-	20	ns/V
		$V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °	C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
VIH	HIGH-level input	$V_{CC} = 1.65 \text{ V}$ to 1.95 V	$0.65V_{CC}$	-	-	0.65V _{CC}	-	V
	voltage	V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		$V_{CC} = 2.7 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	2.0	-	۷
		V_{CC} = 4.5 V to 5.5 V	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
VIL	LOW-level input	$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	-	-	$0.35V_{CC}$	-	$0.35V_{CC}$	۷
	voltage	V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	۷
		$V_{CC} = 2.7 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.8	-	0.8	V
		$V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	I _O = -100 μA; V _{CC} = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	$V_{CC}-0.1$	-	V
	$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	0.95	-	V	
	$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	1.7	-	V	
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	1.9	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	-	-	2.0	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	3.4	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.10	-	0.10	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.30	-	0.45	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.40	-	0.60	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.80	۷
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	-	0.80	V
l	input leakage current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	±0.1	±5	-	±100	μA
OFF	power-off leakage current	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	±0.1	±10	-	±200	μA
СС	supply current	$V_{I} = 5.5 V \text{ or GND}; I_{O} = 0 A;$ $V_{CC} = 1.65 V \text{ to } 5.5 V$	-	0.1	10	-	200	μA
VI _{CC}	additional supply current		-	5	500	-	5000	μA
C _I	input capacitance	$V_{CC} = 3.3 \text{ V};$ $V_{I} = \text{GND to } V_{CC}$	-	3	-	-	-	pF

[1] All typical values are measured at $T_{amb} = 25 \ ^{\circ}C$.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8.

Symbol	Symbol Parameter Conditions			–40 °C to +85 °C			–40 °C to	o +125 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	A, B and C to Y; see Figure 7	[2]						
	V _{CC} = 1.65 V to 1.95 V		1.5	4.7	18.0	1.5	21.5	ns	
		V_{CC} = 2.3 V to 2.7 V		1.0	3.0	6.5	1.0	7.8	ns
		$V_{CC} = 2.7 V$		1.0	3.0	6.0	1.0	7.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.0	2.6	5.0	1.0	6.2	ns
		$V_{CC} = 4.5 V \text{ to } 5.5 V$		1.0	1.9	3.6	1.0	4.4	ns
C_{PD}	power dissipation capacitance	V_{I} = GND to $V_{CC};V_{CC}$ = 3.3 V	[3]	-	12	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

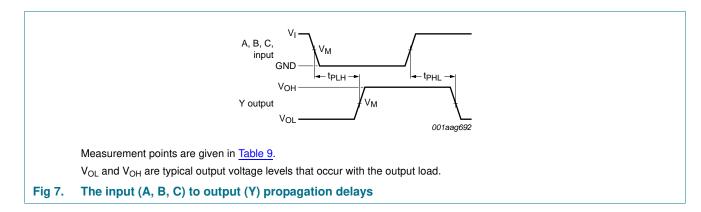
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

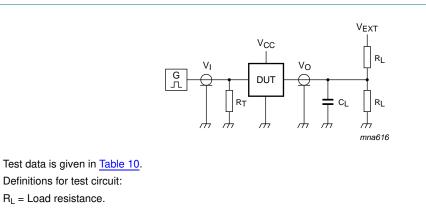
12. Waveforms



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74LVC1G10

Table 9. Measurement points		
Supply voltage	Input	Output
V _{cc}	V _M	V _M
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5V _{CC}	0.5V _{CC}



 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{cc}	VI	$t_r = t_f$	CL	RL	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open

74LVC1G10

Single 3-input NAND gate

13. Package outline

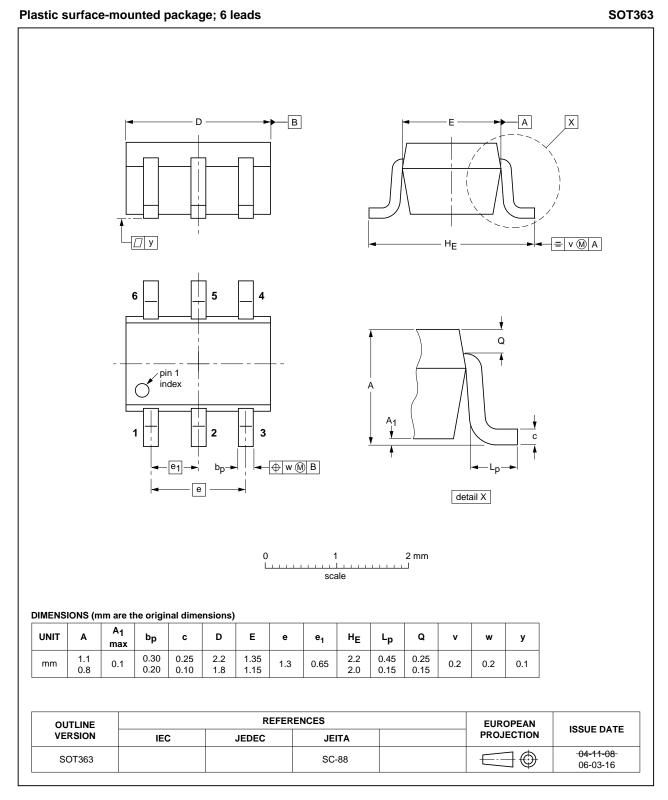


Fig 9. Package outline SOT363 (SC-88)

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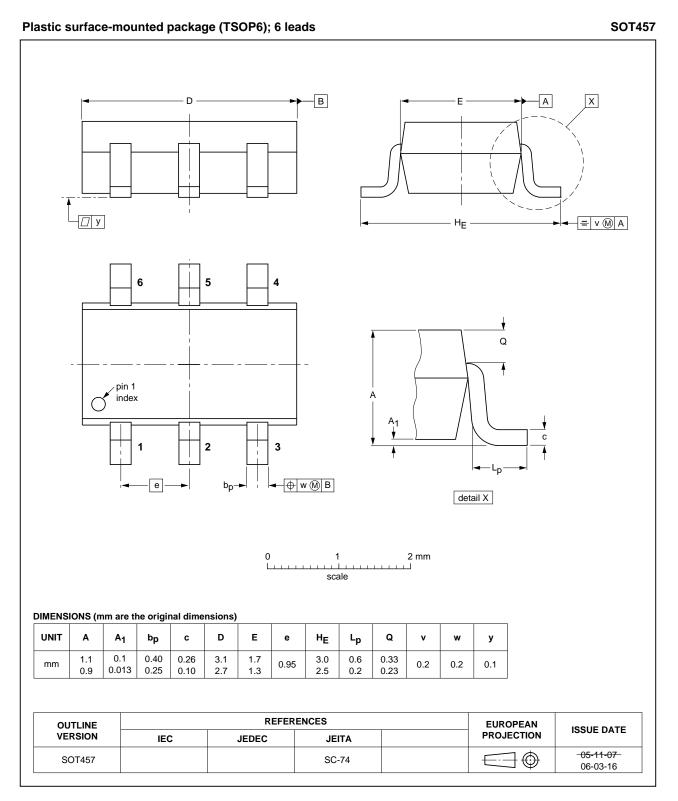
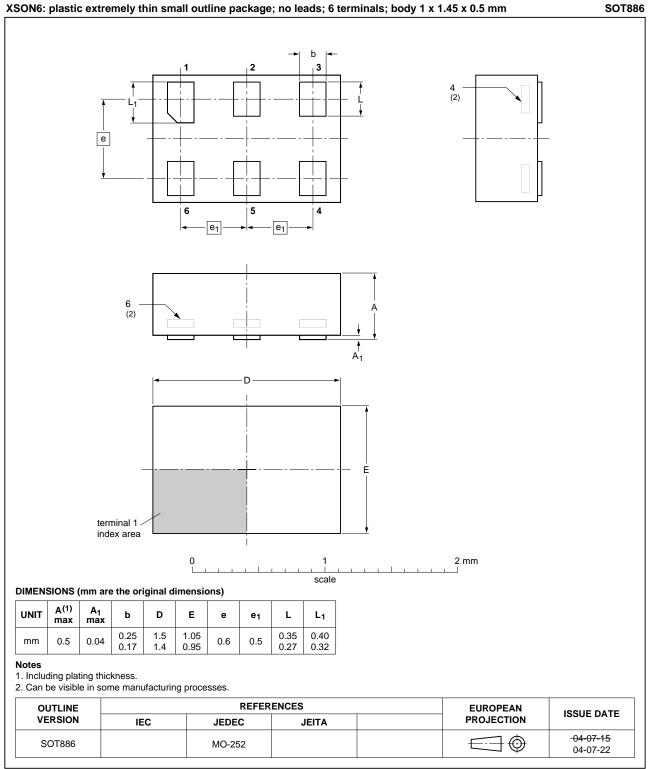


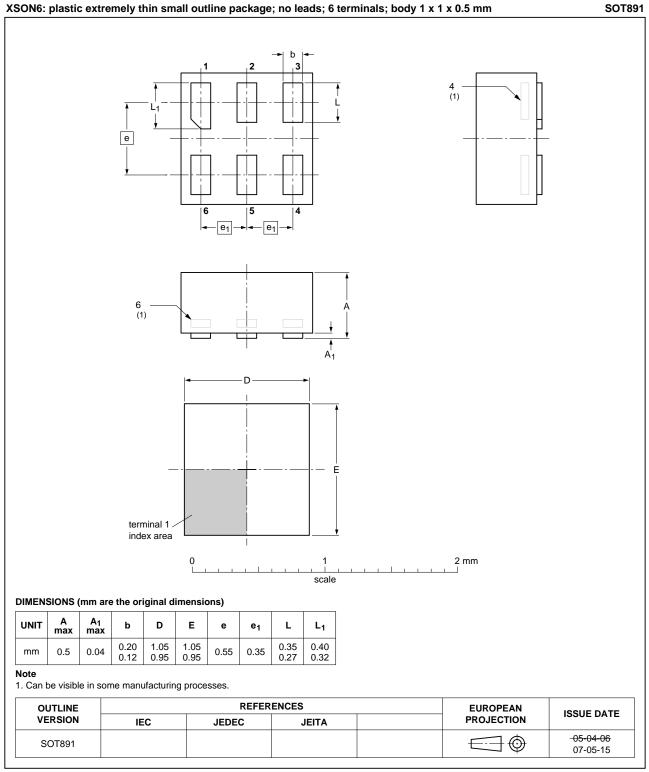
Fig 10. Package outline SOT457 (SC-74)

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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

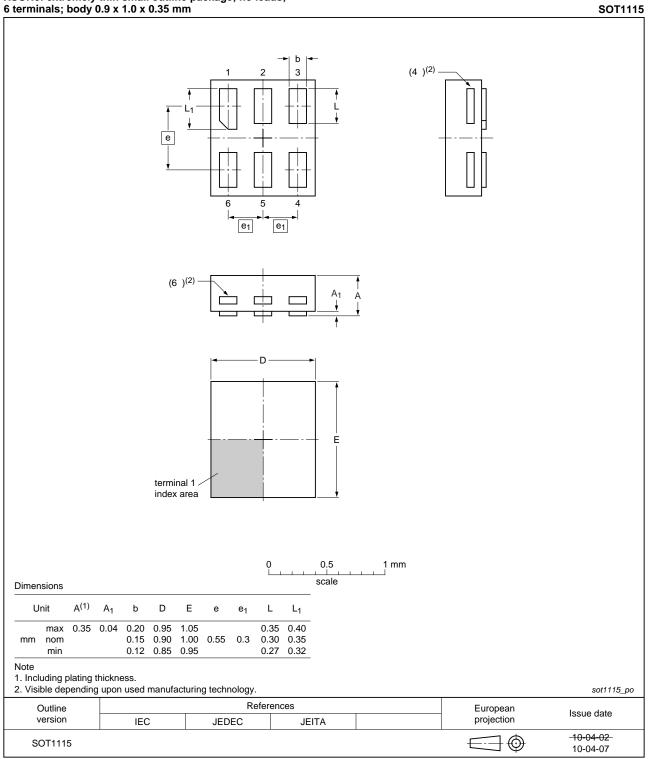
Fig 11. Package outline SOT886 (XSON6)



XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

Fig 12. Package outline SOT891 (XSON6)

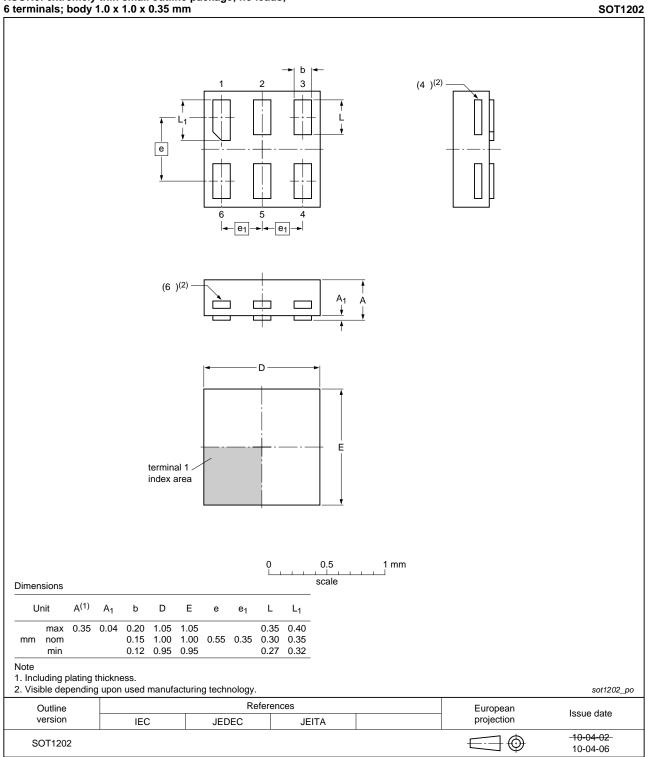
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1202 (XSON6)

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14. Abbreviations

Table 11.	Abbreviations		
Acronym	Description		
CDM	Charged Device Model		
CMOS	Complementary Metal Oxide Semiconductor		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
MM	Machine Model		
TTL	Transistor-Transistor Logic		

15. Revision history

Table 12. Revision	on history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G10 v.3	20111208	Product data sheet	-	74LVC1G10 v.2
Modifications:	 Legal pages 	updated.		
74LVC1G10 v.2	20101021	Product data sheet	-	74LVC1G10 v.1
74LVC1G10 v.1	20071002	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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15 of 17

74LVC1G10

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18. Contents

1	General description 1
2	Features and benefits 1
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning 3
6.2	Pin description 3
7	Functional description 3
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 5
11	Dynamic characteristics 6
12	Waveforms 6
13	Package outline 8
14	Abbreviations 14
15	Revision history 14
16	Legal information 15
16.1	Data sheet status 15
16.2	Definitions 15
16.3	Disclaimers
16.4	Trademarks 16
17	Contact information 16
18	Contents 17

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